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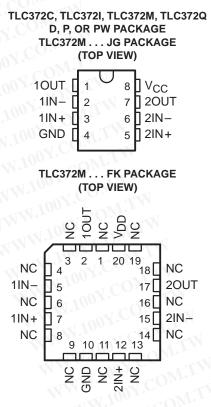
- Single or Dual-Supply Operation
- Wide Range of Supply Voltages 2 V to 18 V
- Very Low Supply Current Drain 150 μA Typ at 5 V
- Fast Response Time . . . 200 ns Typ for TTL-Level Input Step
- Built-in ESD Protection
- High Input Impedance . . . $10^{12} \Omega$ Typ
- Extremely Low Input Bias Current 5 pA Typ
- Ultrastable Low Input Offset Voltage
- Input Offset Voltage Change at Worst-Case Input Conditions Typically 0.23 μV/Month, Including the First 30 Days
- Common-Mode Input Voltage Range
 Includes Ground
- Output Compatible With TTL, MOS, and CMOS
- Pin-Compatible With LM393

description

This device is fabricated using LinCMOSTM technology and consists of two independent voltage comparators, each designed to operate from a single power supply. Operation from dual supplies is also possible if the difference between the two supplies is 2 V to 18 V. Each device features extremely high input impedance (typically greater than $10^{12} \Omega$), allowing direct interfacing with high-impedance sources. The outputs are n-channel open-drain configurations and can be connected to achieve positive-logic wired-AND relationships.

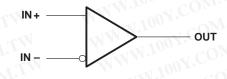
LINCMOSTM DUAL DIFFERENTIAL COMPARATORS SLCS114B – NOVEMBER 1983 – REVISED MARCH 1999

TLC372, TLC372Q, TLC372Y



NC - No internal connection

symbol (each comparator)



The TLC372 has internal electrostatic discharge (ESD) protection circuits and has been classified with a 1000-V ESD rating using human body model testing. However, care should be exercised in handling this device as exposure to ESD may result in a degradation of the device parametric performance.

The TLC372C is characterized for operation from 0°C to 70°C. The TLC372I is characterized for operation from -40°C to 85°C. The TLC372M is characterized for operation over the full military temperature range of -55°C to 125°C. The TLC372Q is characterized for operation from -40°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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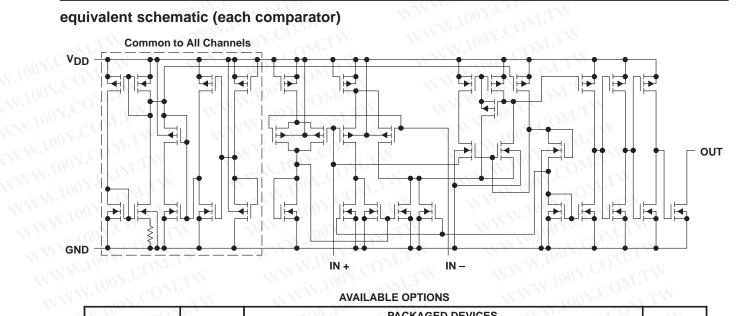
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equivalent schematic (each comparator)



AVAILABLE OPTIONS

V.Jue COJ	1.1	PACKAGED DEVICES							
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)	CHIP FORM (Y)		
0°C to 70°C	5 mV	TLC372CD	TOY.	NT I	TLC372CP	TLC372CPW	TLC372Y		
-40°C to 85°C	5 mV	TLC372ID	You - WW	WT - W	TLC372IP	TOY.C	π		
-55°C to 125°C	5 mV	TLC372MD	TLC372MFK	TLC372MJG	TLC372MP	NN	COME.		
-40°C to 125°C	5 mV	TLC372QD	100	a caller	TLC372QP	ALL INC	CON-		

The D packages are available taped and reeled. Add R suffix to device type (e.g., TLC372CDR). WWW.100Y.COM.TW WWW.100Y.CC WWW.100Y.COM.TW

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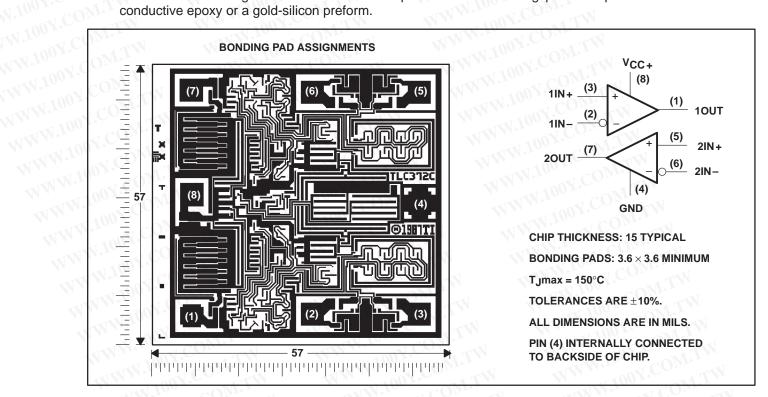
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TLC372Y chip information

These chips, when properly assembled, display characteristics similar to the TLC372C. Thermal compression or ultrasonic bonding can be used on the doped-aluminum bonding pads. Chips can be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Su	pply voltage, V _{DD} (see Note 1)
	ferential input voltage, VID (see Note 2±18 V
	but voltage range, VI
O	Itput voltage, Vo
	but current, I ₁
	itput current, I _O
	ration of output short circuit to ground (see Note 3) unlimited
	ntinuous total power dissipation
	perating free-air temperature range, T _A : TLC372C
Y.C	TLC372I
	TLC372M
	TLC372Q
Ste	prage temperature range
	se temperature for 60 seconds: FK package
	ad temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, P, or PW package
	ad temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values except differential voltages are with respect to network ground.

2. Differential voltages are at IN+ with respect to IN -.

3. Short circuits from outputs to V_{DD} can cause excessive heating and eventual device destruction.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	500 mW	5.8 mW/°C	64°C	464 mW	377 mW	145 mW
FK	500 mW	11.0 mW/°C	104°C	500 mW	500 mW	275 mW
JG	500 mW	8.4 mW/°C	90°C	500 mW	500 mW	210 mW
P	500 mW	8.0 mW/°C	87°C	500 mW	500 mW	200 mW
PW	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A

recommended operating conditions

WWWW. OOX.C	WT	TLC3	72C	TLC	3721	TLC3	72M	TLC3	72Q	UNIT
WW.Ioo V	OM.	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	NOY.
Supply voltage, V _{DD}	COM.	3	16	3	16	4	16	4	16	V
Common mode input veltage Wig100	V _{DD} = 5 V	0	3.5	0	3.5	0	3.5	0	3.5	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	0	8.5	0	8.5	0	8.5	0	8.5	
perating free-air temperature, TA	ST CONT.	0	70	-40	85	-55	125	-40	125	°C

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		TECT CON	DITIONS	CONT	TL	C372C			.C372I		TLC372	N, TLC3	372Q	
	PARAMETER	TEST COM	NDITIONS 001	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V. 2		Vie Viermin	See Note 1	25°C	N	1	5	1001.0	1	5		1	5	mV
VIO	Input offset voltage	$V_{IC} = V_{ICR}min$,	See Note 4	Full range	IN	1	6.5	.Vool	<u><u></u></u>	7			10	mv
	Input offect ourrest		W.10	25°C		1	VIA	1.100	c01			1		pА
10	Input offset current	WIN		MAX	1.7.1		0.3	N.100 1	202	1			10	nA
L.=	ANN CU	WT	MW.	25°C	WTT	5	MI	100	5	TIM		5		pА
IВ	Input bias current	M. I		MAX	W. T		0.6	111.2	V.CU	2	N		20	nA
Vien	Common-mode input	OM.I.W	WWV	25°C	0 to V _{DD} -1		V	0 to V _{DD} -1	oy.C	0 <i>br</i> .	0 to V _{DD} -1			v
VICR	voltage range	CONTR		Full range	0 to V _{DD} -1.5	N	1	0 to V _{DD} -1.5	00Y.		0 to V _{DD} -1.5			V
1	Link Intel autout autout	CONTRACTOR	V _{OH} = 5 V	25°C		0.1		du.	0.1		WT.L	0.1		nA
ЮН	High-level output current	V _{ID} = 1 V	V _{OH} = 15 V	Full range	COM	W	1	WWW		<u>.</u> C1	WT		3	μA
M		N CAN	1	25°C	- cOM	150	400		150	400	ON.	150	400	mV
VOL	Low-level output voltage	$V_{ID} = -1 V$,	IOL = 4 mA	Full range	11.	1.1.1	700	N.	N.10	700	OM.		700	mv
IOL	Low-level output current	$V_{ID} = -1 V$,	V _{OL} = 1.5 V	25°C	6	16	N	6	16	001.	6	16		mA
1	Supply current	V-SAVONA	Nolood	25°C	OJ.VO	150	300	N/	150	300	COm	150	300	
IDD	(two comparators)	V _{ID} = 1 V,	No load	Full range	100	Э <i>М</i> .,	400		WAR	400	1 CON.		400	μA

electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

⁺ All characteristics are measured with zero common-mode input voltage unless otherwise noted. Full range is 0°C to 70°C for TLC372C, -40°C to 85°C for TLC372I, and -55°C to 125°C for TLC372M and -40°C to 125°C for TLC372Q. IMPORTANT: See Parameter Measurement Information.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, V_{DD} = 5 V, T_A = 25°C

PARAMETER	TEST C	CONDITIONS		MIN	TYP	MAX	UNIT
Deenenee time	R _L connected to 5 V through 5.1 kΩ, C _L = 15 pF [‡] ,	100-mV input step with 5-mV overdrive	WW.	100%	650	$\Lambda T N$	
Response time	See Note 5	TTL-level input step	WWV		200	1	ns

[‡]C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses 1.4 V.

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TLC372,

TLC372Q, TLC372Y

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electrical characteristics at specified free-air temperature, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

VIOInput offset voltage $V_{IC} = V_{ICR}min$, See Note 41IIOInput offset current1IIBInput bias current5VICRCommon-mode input voltage range0 to $V_{DD}-1$ IOHHigh-level output current $V_{ID} = 1 V$, $V_{OH} = 5 V$ 0.1VOLLow-level output voltage $V_{ID} = -1 V$, $I_{OL} = 4 mA$ 150			TLC372Y	IDITIONET	TEST COL	DADAMETED	
Input offset current 1 Input bias current 5 VICR Common-mode input voltage range $0 \text{ to } V_{DD-1}$ IOH High-level output current VID = 1 V, V_{OH} = 5 V 0.1 VOL Low-level output voltage VID = -1 V, IOL = 4 mA 150 40		MAX	MIN TYP	NDITIONS	TEST CO	PARAMETER	
Input bias current 5 VICR Common-mode input voltage range 0 to $V_{DD}-1$ IOH High-level output current VID = 1 V, VOH = 5 V 0.1 VOL Low-level output voltage VID = -1 V, IOL = 4 mA 150 40	mV	5	1	See Note 4	VIC = VICRmin,	Input offset voltage)
VICRCommon-mode input voltage range0 to $V_{DD}-1$ IOHHigh-level output current $V_{ID} = 1 V$, $V_{OH} = 5 V$ 0.1VOLLow-level output voltage $V_{ID} = -1 V$, $I_{OL} = 4 \text{ mA}$ 15040	pА		1	11004.00	All All	Input offset current	Or
VICRCommon-mode input voltage range $V_{DD}-1$ IOHHigh-level output current $V_{ID} = 1 V$, $V_{OH} = 5 V$ 0.1 VOLLow-level output voltage $V_{ID} = -1 V$, $I_{OL} = 4 \text{ mA}$ $150 40$	pА		5	NW. SONY.C	VVI VV	Input bias current	c0
V_{OL} Low-level output voltage $V_{ID} = -1 V$, $I_{OL} = 4 mA$ 150 40	V			WW.100Y.	W W	Common-mode input voltage range	CR
	nA		0.1	V _{OH} = 5 V	V _{ID} = 1 V,	High-level output current	47 (
$V_{ID} = -1 V$, $V_{OI} = 1.5 V$ 6 16	mV	400	150	$I_{OL} = 4 \text{ mA}$	$V_{ID} = -1 V,$	Low-level output voltage)L
OE OE	mA		6 16	V _{OL} = 1.5 V	$V_{ID} = -1 V,$	Low-level output current	NO1
I_{DD} Supply current (two comparators) $V_{ID} = 1 V$, No load 150 30	μΑ	300	150	No load	V _{ID} = 1 V,	Supply current (two comparators)	D

[†] All characteristics are measured with zero common-mode input voltage unless otherwise noted. IMPORTANT: See Parameter Measurement Information.

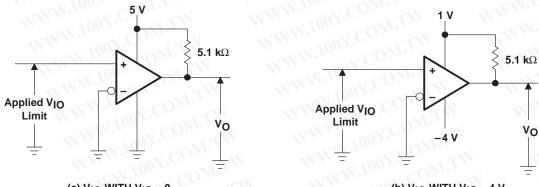
The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor NOTE 4: between the output and VDD. They can be verified by applying the limit value to the input and checking for the appropriate output state.

PARAMETER MEASUREMENT INFORMATION

The digital output stage of the TLC372 can be damaged if it is held in the linear region of the transfer curve. Conventional operational amplifier/comparator testing incorporates the use of a servo loop that is designed to force the device output to a level within this linear region. Since the servo-loop method of testing cannot be used, the following alternatives for measuring parameters such as input offset voltage, common-mode rejection, etc., are offered.

To verify that the input offset voltage falls within the limits specified, the limit value is applied to the input as shown in Figure 1(a). With the noninverting input positive with respect to the inverting input, the output should be high. With the input polarity reversed, the output should be low.

A similar test can be made to verify the input offset voltage at the common-mode extremes. The supply voltages can be slewed as shown in Figure 1(b) for the V_{ICR} test, rather than changing the input voltages, to provide greater accuracy.



(a) VIO WITH VIC = 0

(b) V_{IO} WITH $V_{IC} = 4 V$

Figure 1. Method for Verifying That Input Offset Voltage is Within Specified Limits

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PARAMETER MEASUREMENT INFORMATION

A close approximation of the input offset voltage can be obtained by using a binary search method to vary the differential input voltage while monitoring the output state. When the applied input voltage differential is equal, but opposite in polarity, to the input offset voltage, the output changes states.

Figure 2 illustrates a practical circuit for direct dc measurement of input offset voltage that does not bias the comparator into the linear region. The circuit consists of a switching-mode servo loop in which U1a generates a triangular waveform of approximately 20-mV amplitude. U1b acts as a buffer, with C2 and R4 removing any residual dc offset. The signal is then applied to the inverting input of the comparator under test, while the noninverting input is driven by the output of the integrator formed by U1c through the voltage divider formed by R9 and R10. The loop reaches a stable operating point when the output of the comparator under test has a duty cycle of exactly 50%, which can only occur when the incoming triangle wave is sliced symmetrically or when the voltage at the noninverting input exactly equals the input offset voltage.

Voltage divider R9 and R10 provides a step up of the input offset voltage by a factor of 100 to make measurement easier. The values of R5, R8, R9, and R10 can significantly influence the accuracy of the reading; therefore, it is suggested that their tolerance level be 1% or lower.

Measuring the extremely low values of input current requires isolation from all other sources of leakage current and compensation for the leakage of the test socket and board. With a good picoammeter, the socket and board leakage can be measured with no device in the socket. Subsequently, this open-socket leakage value can be subtracted from the measurement obtained with a device in the socket to obtain the actual input current of the device.

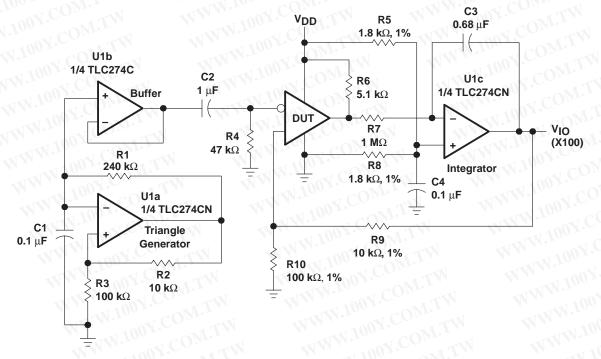


Figure 2. Circuit for Input Offset Voltage Measurement

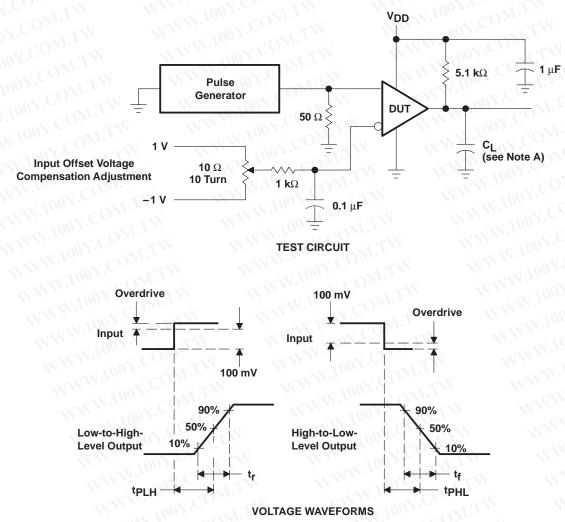
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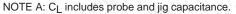


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PARAMETER MEASUREMENT INFORMATION

Response time is defined as the interval between the application of an input step function and the instant when the output reaches 50% of its maximum value. Response time, low-to-high-level output, is measured from the leading edge of the input pulse, while response time, high-to-low-level output, is measured from the trailing edge of the input pulse. Response-time measurement at low input signal levels can be greatly affected by the input offset voltage. The offset voltage should be balanced by the adjustment at the inverting input as shown in Figure 3, so that the circuit is just at the transition point. Then a low signal, for example 105-mV or 5-mV overdrive, causes the output to change state.







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PRINCIPLES OF OPERATION

LinCMOS[™] process

The LinCMOS[™] process is a Linear polysilicon-gate complementary-MOS process. Primarily designed for single-supply applications, LinCMOS[™] products facilitate the design of a wide range of high-performance analog functions, from operational amplifiers to complex mixed-mode converters.

While digital designers are experienced with CMOS, MOS technologies are relatively new for analog designers. This short guide is intended to answer the most frequently asked questions related to the quality and reliability of LinCMOS[™] products. Further questions should be directed to the nearest TI field sales office.

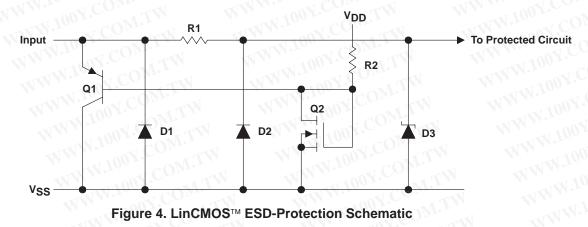
electrostatic discharge

CMOS circuits are prone to gate oxide breakdown when exposed to high voltages even if the exposure is only for very short periods of time. Electrostatic discharge (ESD) is one of the most common causes of damage to CMOS devices. It can occur when a device is handled without proper consideration for environmental electrostatic charges, e.g. during board assembly. If a circuit in which one amplifier from a dual operational amplifier is being used and the unused pins are left open, high voltages tends to develop. If there is no provision for ESD protection, these voltages may eventually punch through the gate oxide and cause the device to fail. To prevent voltage buildup, each pin is protected by internal circuitry.

Standard ESD-protection circuits safely shunt the ESD current by providing a mechanism whereby one or more transistors break down at voltages higher than the normal operating voltages but lower than the breakdown voltage of the input gate. This type of protection scheme is limited by leakage currents which flow through the shunting transistors during normal operation after an ESD voltage has occurred. Although these currents are small, on the order of tens of nanoamps, CMOS amplifiers are often specified to draw input currents as low as tens of picoamps.

To overcome this limitation, TI design engineers developed the patented ESD-protection circuit shown in Figure 4. This circuit can withstand several successive 1-kV ESD pulses, while reducing or eliminating leakage currents that may be drawn through the input pins. A more detailed discussion of the operation of TI's ESD-protection circuit is presented on the next page.

All input and output pins on LinCMOS and Advanced LinCMOS[™] products have associated ESD-protection circuitry that undergoes qualification testing to withstand 1000 V discharged from a 100-pF capacitor through a 1500-Ω resistor (human body model) and 200 V from a 100-pF capacitor with no current-limiting resistor (charged device model). These tests simulate both operator and machine handling of devices during normal test and assembly operations.



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PRINCIPLES OF OPERATION

input protection circuit operation

Texas Instruments patented protection circuitry allows for both positive-and negative-going ESD transients. These transients are characterized by extremely fast rise times and usually low energies, and can occur both when the device has all pins open and when it is installed in a circuit.

positive ESD transients

Initial positive charged energy is shunted through Q1 to V_{SS}. Q1 turns on when the voltage at the input rises above the voltage on the V_{DD} pin by a value equal to the V_{EB} of Q1. The base current increases through R2 with input current as Q1 saturates. The base current through R2 forces the voltage at the drain and gate of Q2 to exceed its threshold level (V_T ~ 22 V to 26 V) and turn Q2 on. The shunted input current through Q1 to V_{SS} is now shunted through the n-channel enhancement-type MOSFET Q2 to V_{SS}. If the voltage on the input pin continues to rise, the breakdown voltage of the zener diode D3 is exceeded, and all remaining energy is dissipated in R1 and D3. The breakdown voltage of D3 is designed to be 24 to 27 V, which is well below the gate oxide voltage of the circuit to be protected.

negative ESD transients

The negative charged ESD transients are shunted directly through D1. Additional energy is dissipated in R1 and D2 as D2 becomes forward biased. The voltage seen by the protected circuit is -0.3 V to -1 V (the forward voltage of D1 and D2).

circuit-design considerations

LinCMOSTM products are being used in actual circuit environments that have input voltages that exceed the recommended common-mode input voltage range and activate the input protection circuit. Even under normal operation, these conditions occur during circuit power up or power down, and in many cases, when the device is being used for a signal conditioning function. The input voltages can exceed V_{ICR} and not damage the device only if the inputs are current limited. The recommended current limit shown on most product data sheets is ± 5 mA. Figures 5 and 6 show typical characteristics for input voltage versus input current.

Normal operation and correct output state can be expected even when the input voltage exceeds the positive supply voltage. Again, the input current should be externally limited even though internal positive current limiting is achieved in the input protection circuit by the action of Q1. When Q1 is on, it saturates and limits the current to approximately 5-mA collector current by design. When saturated, Q1 base current increases with input current. This base current is forced into the V_{DD} pin and into the device I_{DD} or the V_{DD} supply through R2 producing the current limiting effects shown in Figure 5. This internal limiting lasts only as long as the input voltage is below the V_T of Q2.

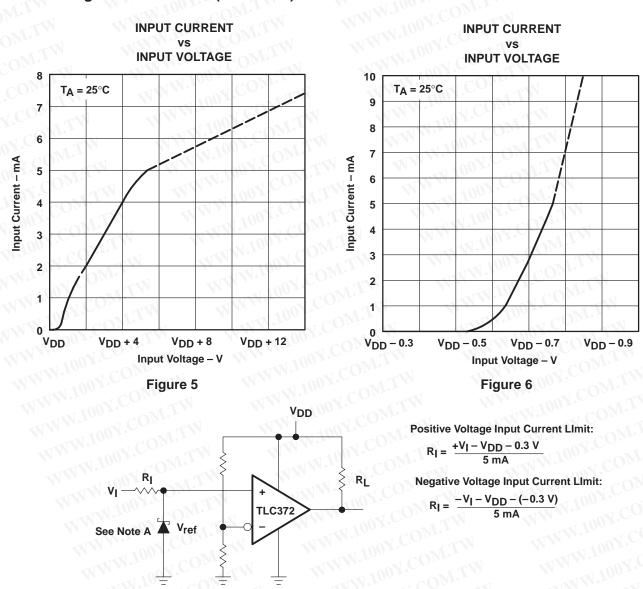
When the input voltage exceeds the negative supply voltage, normal operation is affected and output voltage states may not be correct. Also, the isolation between channels of multiple devices (duals and quads) can be severely affected. External current limiting must be used since this current is directly shunted by D1 and D2 and no internal limiting is achieved. If normal output voltage states are required, an external input voltage clamp is required (see Figure 7).

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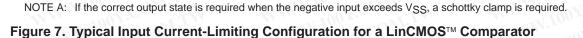


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PRINCIPLES OF OPERATION



circuit-design considerations (continued)



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